

ABSTRACT OF THE DISCLOSURE

In a p-type base layer of a trench IGBT comprising
a p-type collector layer, an n-type base layer formed
on the p-type collector layer, the p-type base layer
5 formed on the n-type base layer, and an n-type emitter
layer formed on the surface of the p-type base layer,
the point of the highest impurity concentration is
located closer to the n-type base layer than the
junction with the emitter layer. In other words, the
10 pinch-off of the channel is generated in the position
closer to the n-type base layer than to the junction
between the p-type base layer and the n-type emitter
layer.